

30 A - 600 V - short circuit rugged IGBT

Features

- Low on-voltage drop ($V_{CE(sat)}$)
- Low C_{res} / C_{ies} ratio (no cross conduction susceptibility)
- Short circuit withstand time 10 μs

Applications

- High frequency inverters
- Motor drivers

Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

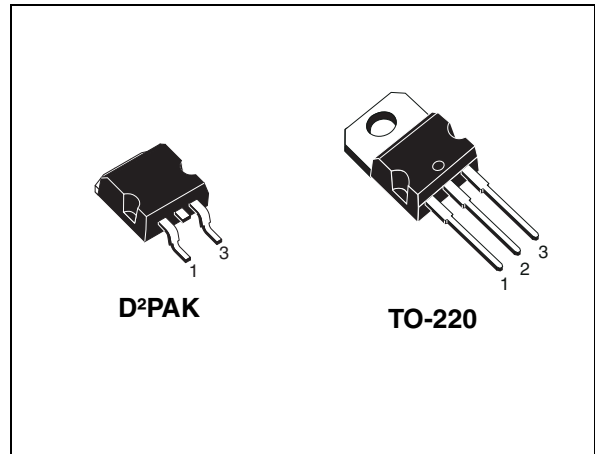


Figure 1. Internal schematic diagram

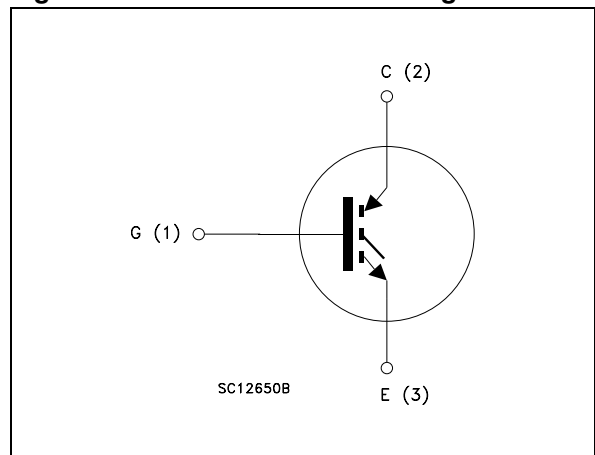


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB30NC60KT4	GB30NC60K	D²PAK	Tape and reel
STGP30NC60K	GP30NC60K	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$)	600	V
$I_C^{(1)}$	Collector current (continuous) at $T_C = 25^\circ\text{C}$	60	A
$I_C^{(1)}$	Collector current (continuous) at $T_C = 100^\circ\text{C}$	26	A
$I_{CL}^{(2)}$	Turn-off latching current	125	A
$I_{CP}^{(3)}$	Pulsed collector current	125	A
V_{GE}	Gate-emitter voltage	± 20	V
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	185	W
t_{scw}	Short circuit withstand time, $V_{CE} = 0.5V_{(BR)CES}$ $T_j = 125^\circ\text{C}$, $R_G = 10\ \Omega$, $V_{GE} = 12\ \text{V}$	10	μs
T_j	Operating junction temperature	- 55 to 150	$^\circ\text{C}$

1. Calculated according to the iterative formula:

$$I_c(T_c) = \frac{T_{J(MAX)} - T_c}{R_{thj-c} \times V_{CE(sat)(MAX)} \cdot (T_c, I_c)}$$

2. $V_{clamp} = 80\%, (V_{CES})$, $T_j = 150^\circ\text{C}$, $R_G = 10\ \Omega$, $V_{GE} = 15\ \text{V}$
 3. Pulse width limited by max. junction temperature allowed

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max.	0.675	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max.	62.5	$^\circ\text{C/W}$

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE}=0$)	$I_C=1\text{ mA}$	600			V
$V_{CE(SAT)}$	Collector-emitter saturation voltage	$V_{GE}=15\text{ V}$, $I_C=20\text{ A}$		2.1	2.7	V
		$V_{GE}=15\text{ V}$, $I_C=20\text{ A}$, $T_C=125^{\circ}\text{C}$		1.9		V
I_{CES}	Collector cut-off current ($V_{GE}=0$)	$V_{CE}=600\text{ V}$ $V_{CE}=600\text{ V}$, $T_C=125^{\circ}\text{C}$			150 1	μA mA
$V_{GE(th)}$	Gate threshold voltage	$V_{CE}=V_{GE}$, $I_C=250\text{ }\mu\text{A}$	4.5		6.5	V
I_{GES}	Gate-emitter cut-off current ($V_{CE}=0$)	$V_{GE}=\pm 20\text{ V}$			± 100	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE}=15\text{ V}$, $I_C=20\text{ A}$		15		S

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE}=25\text{ V}$, $f=1\text{ MHz}$, $V_{GE}=0$		2170		pF
C_{oes}	Output capacitance			230		pF
C_{res}	Reverse transfer capacitance			46		pF
Q_g	Total gate charge	$V_{CE}=480\text{ V}$, $I_C=20\text{ A}$,		96		nC
Q_{ge}	Gate-emitter charge	$V_{GE}=15\text{ V}$		18		nC
Q_{gc}	Gate-collector charge	(see Figure 17)		46		nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$		29		ns
t_r	Current rise time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$		12		ns
$(di/dt)_{on}$	Turn-on current slope	(see Figure 16)		1520		A/ μ s
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$		27		ns
t_r	Current rise time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$,		14		ns
$(di/dt)_{on}$	Turn-on current slope	$T_C = 125^\circ\text{C}$ (see Figure 16)		1360		A/ μ s
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$,		36		ns
$t_{d(off)}$	Turn-off delay time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$		120		ns
t_f	Current fall time	(see Figure 16)		85		ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$,		75		ns
$t_{d(off)}$	Turn-off delay time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$		160		ns
t_f	Current fall time	$T_C = 125^\circ\text{C}$ (see Figure 16)		130		ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
E_{on}	Turn-on switching losses	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$		350		μ J
$E_{off}^{(1)}$	Turn-off switching losses	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$,		435		μ J
E_{ts}	Total switching losses	(see Figure 16)		785		μ J
E_{on}	Turn-on switching losses	$V_{CC} = 480\text{ V}$, $I_C = 20\text{ A}$		590		μ J
$E_{off}^{(1)}$	Turn-off switching losses	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$,		845		μ J
E_{ts}	Total switching losses	$T_C = 125^\circ\text{C}$ (see Figure 16)		1435		μ J

1. Turn-off losses include also the tail of the collector current.

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

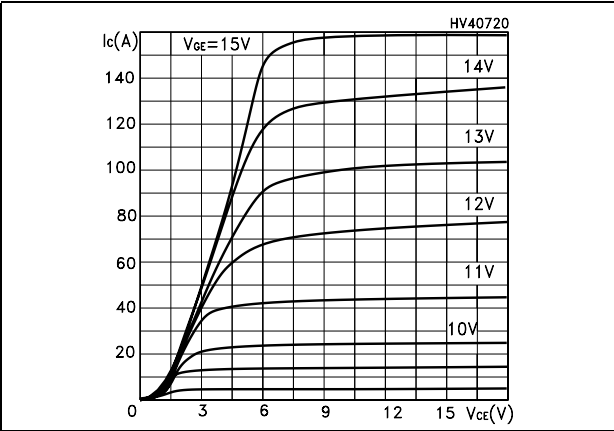


Figure 3. Transfer characteristics

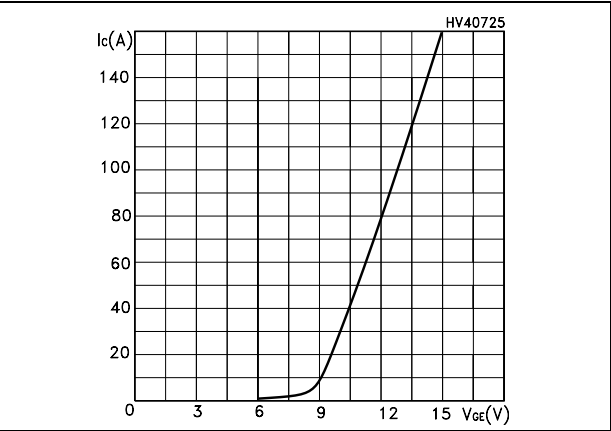


Figure 4. Transconductance

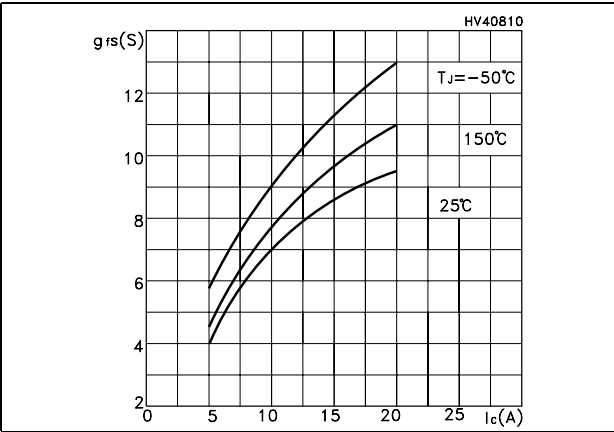


Figure 5. Collector-emitter on voltage vs temperature

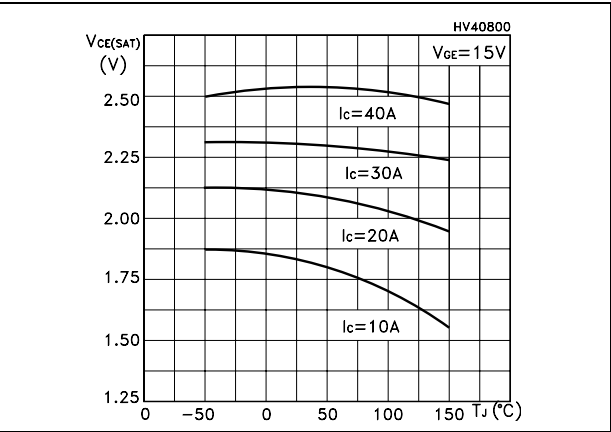


Figure 6. Gate charge vs gate-source voltage

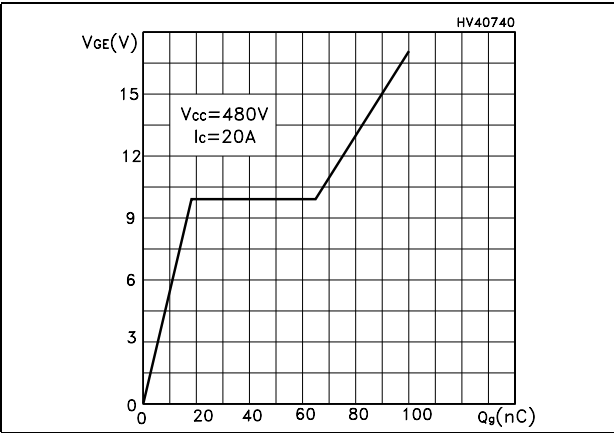


Figure 7. Capacitance variations

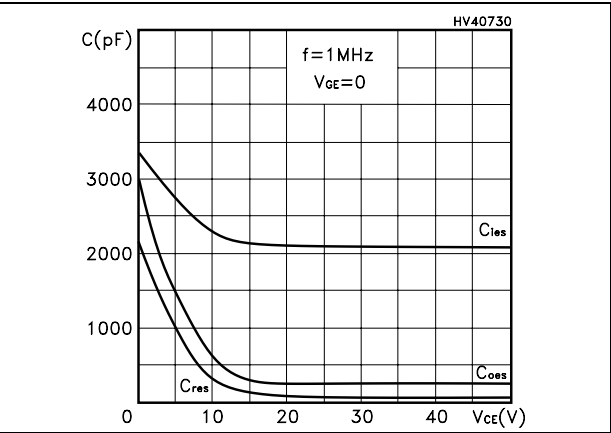


Figure 8. Normalized gate threshold voltage vs temperature

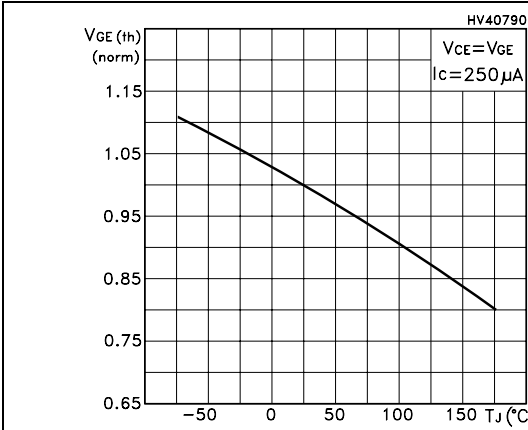


Figure 9. Collector-emitter on voltage vs collector current

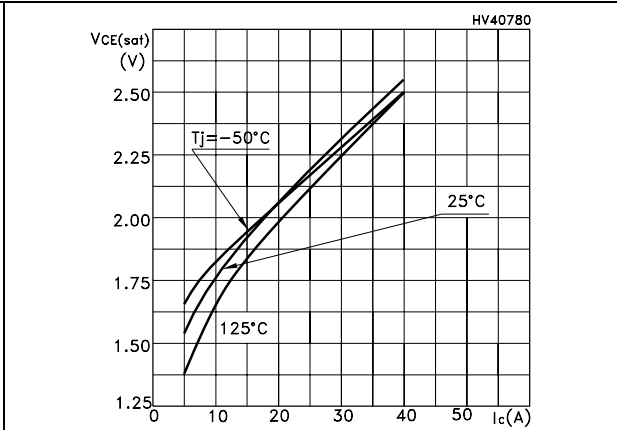


Figure 10. Normalized breakdown voltage vs temperature

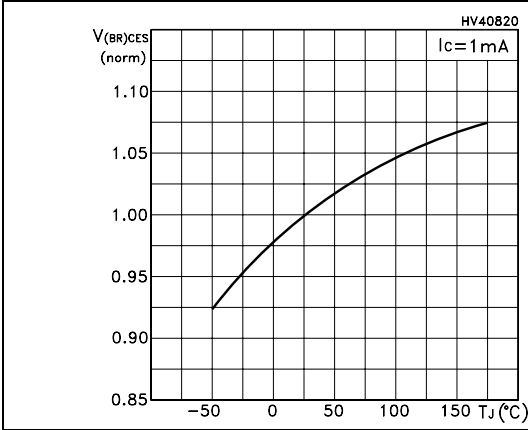


Figure 11. Switching losses vs temperature

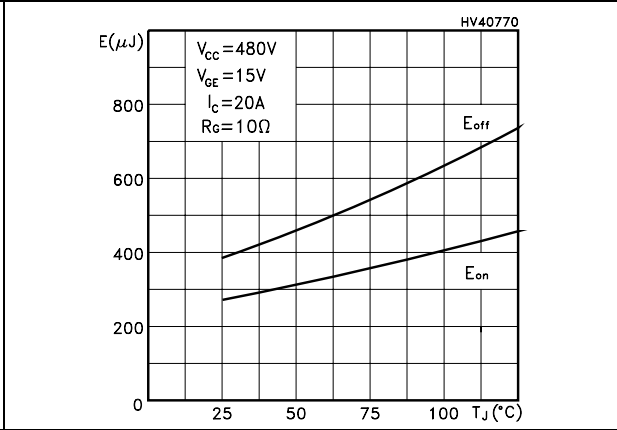


Figure 12. Switching losses vs gate resistance

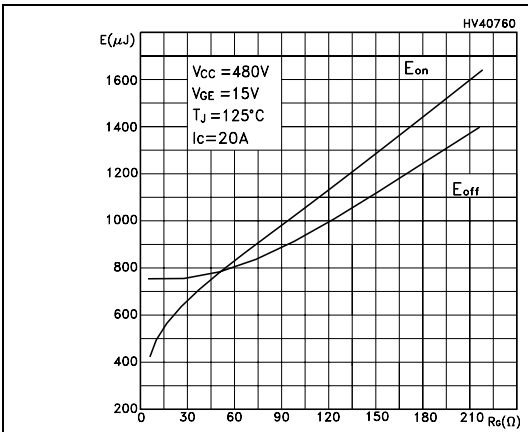


Figure 13. Switching losses vs collector current

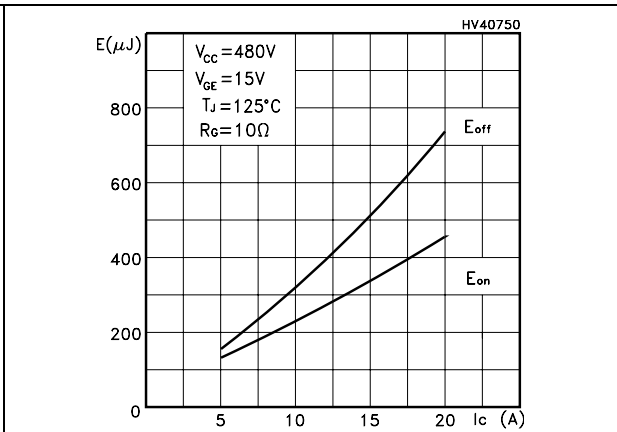


Figure 14. Thermal Impedance

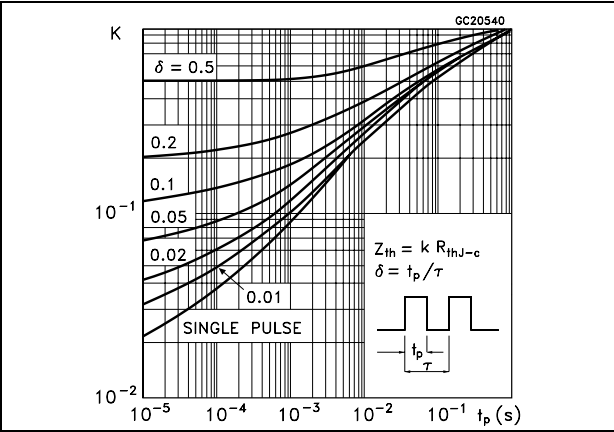
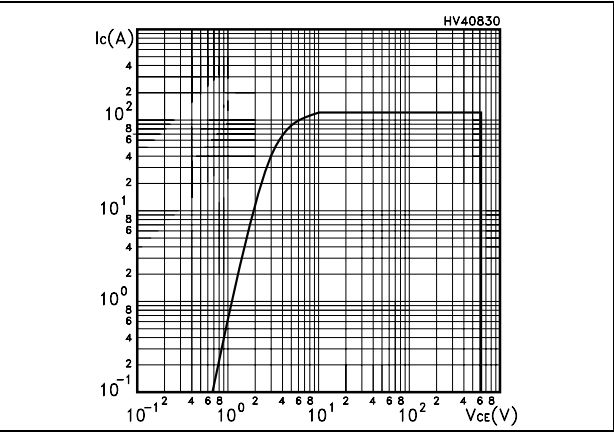


Figure 15. Turn-off SOA



3 Test circuit

Figure 16. Test circuit for inductive load switching

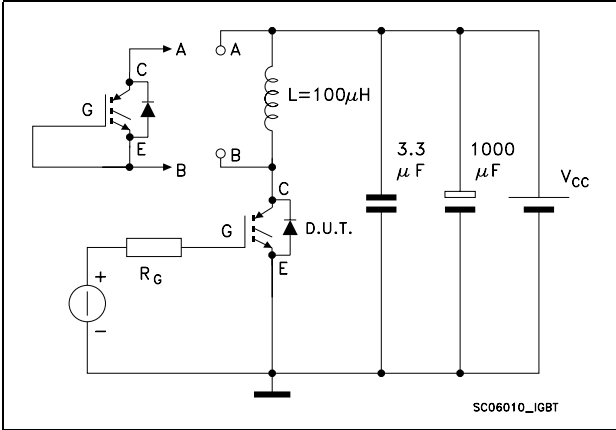


Figure 17. Gate charge test circuit

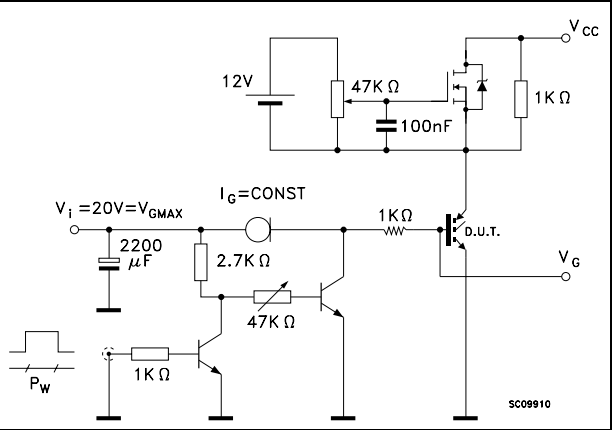
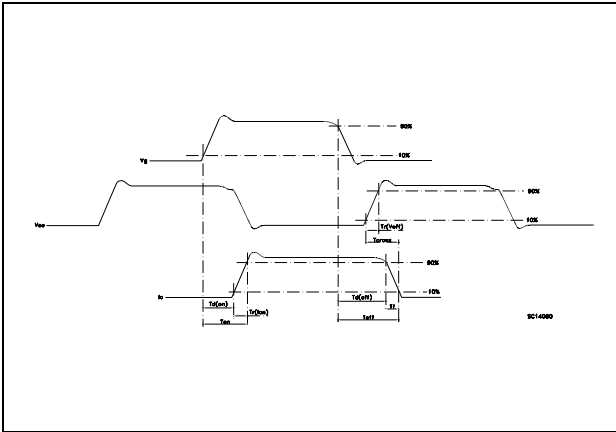


Figure 18. Switching waveforms

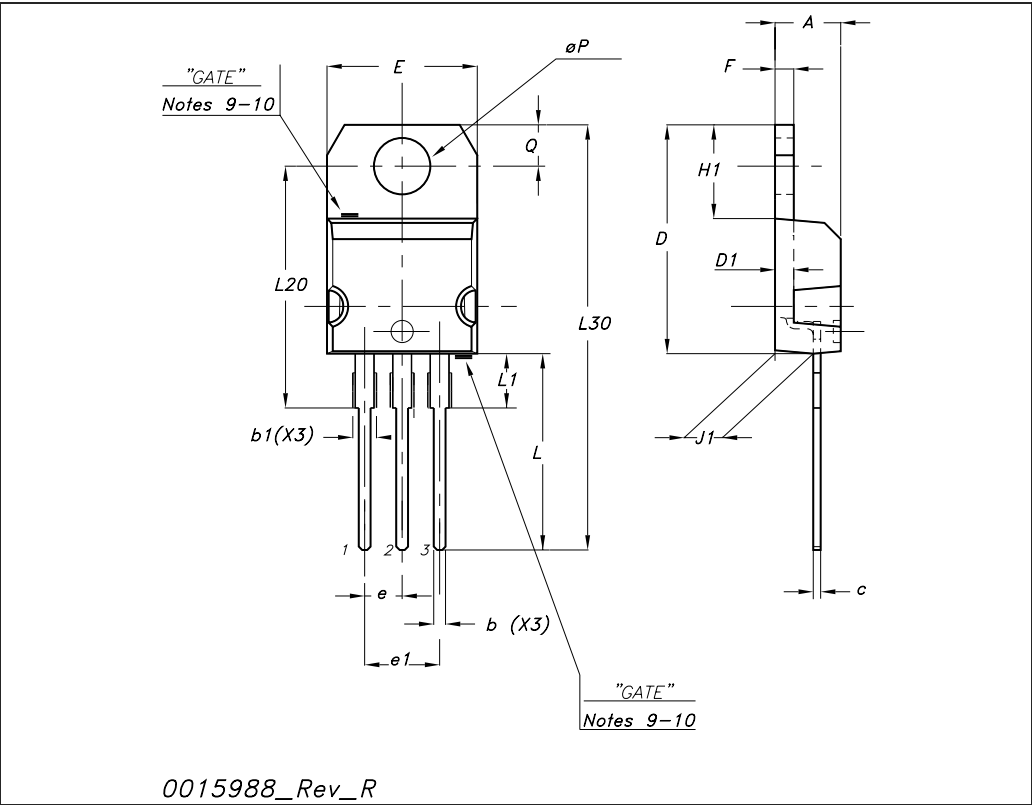


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

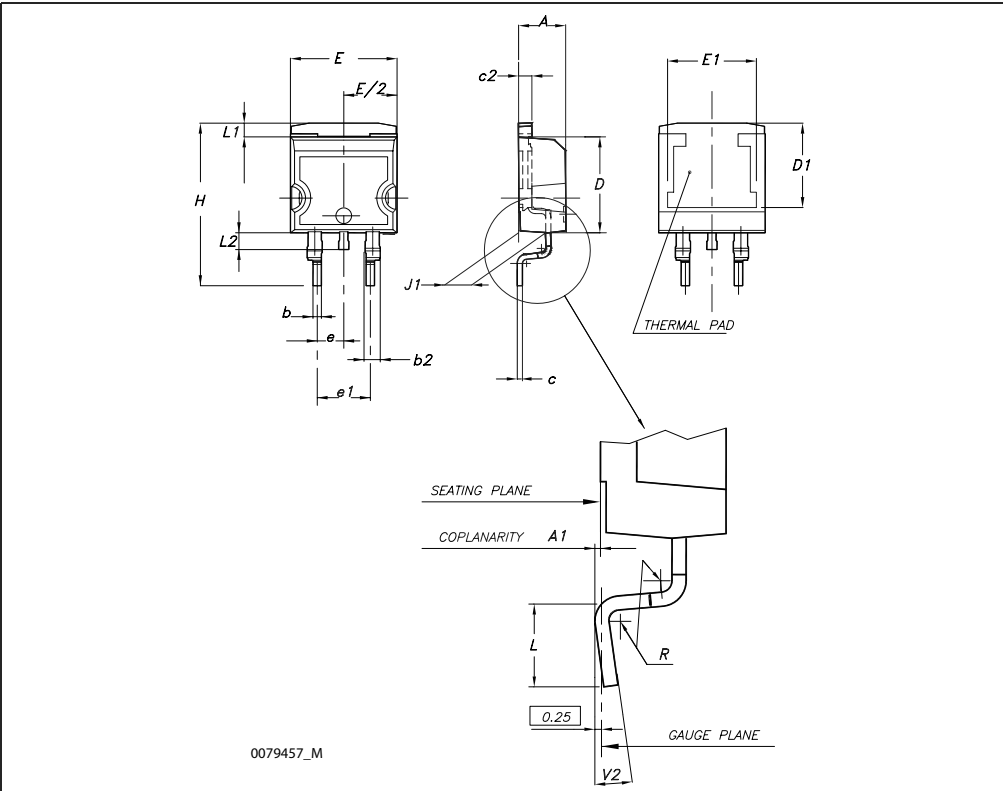
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



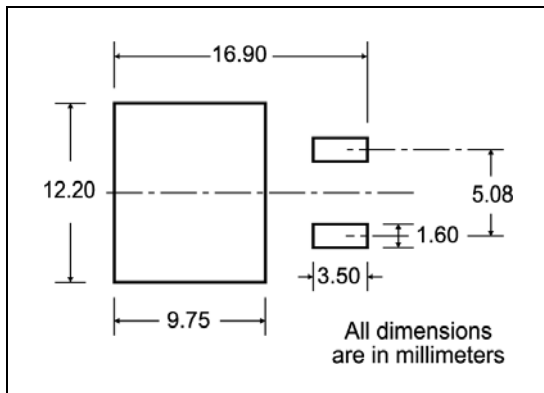
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

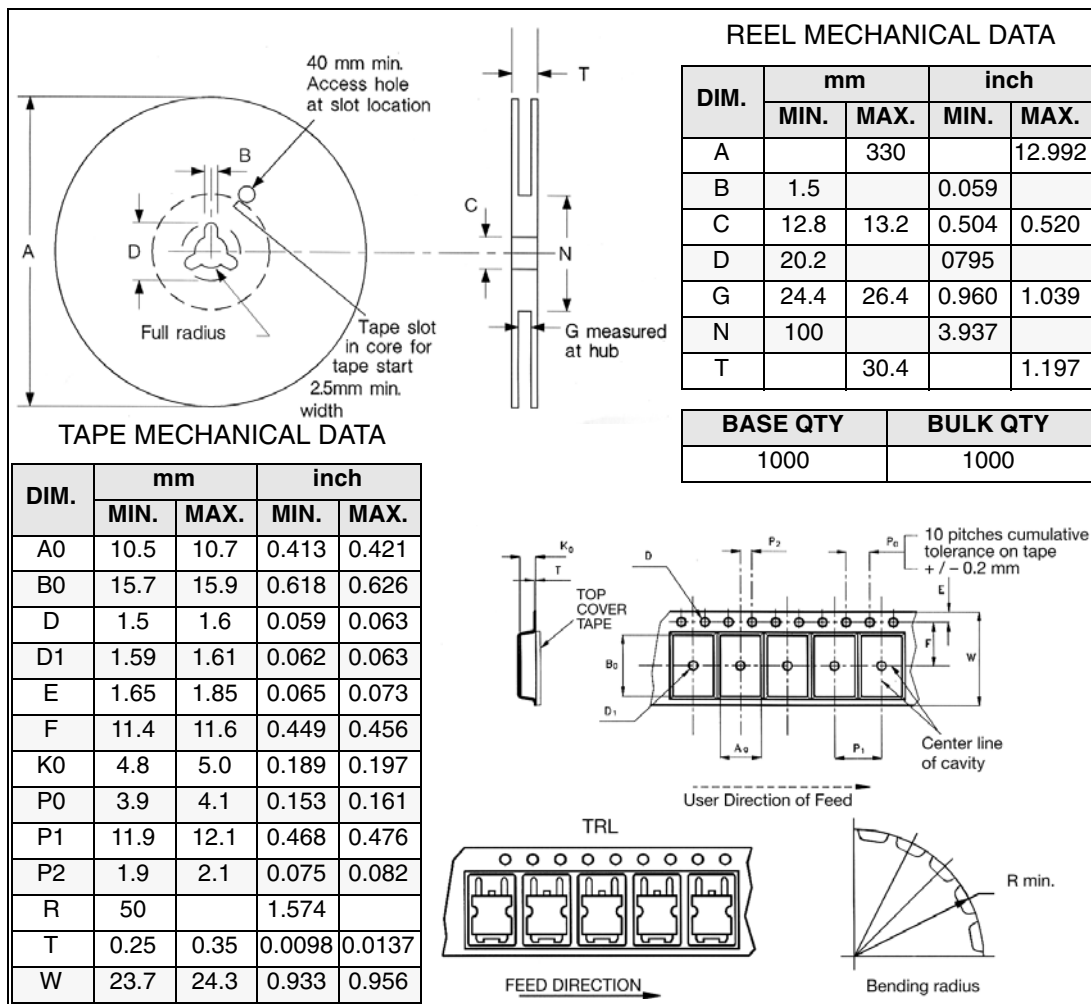


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
12-Feb-2008	1	Initial release
07-Mar-2008	2	Updated mechanical data for both packages

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